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## Single-Photon Emitters in Lead-Implanted Single-Crystal Diamond

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ABSTRACT: We report on the creation and characterization of Pb-related color centers in diamond upon ion implantation and subsequent thermal annealing. Their optical emission in the photoluminescence (PL) regime consists of an articulated spectrum with intense emission peaks at 552.1 and 556.8 nm, accompanied by a set of additional lines in the 535-700 nm range. The attribution of the PL emission to stable Pb-based defects is corroborated by the correlation of its intensity with the implantation fluence of Pb ions. PL measurements performed as a function of sample temperature (in the 143-300 K range) and under different excitation wavelengths (i.e., 532, 514, 405 nm) suggest that the complex spectral features observed in Pb-implanted diamond might be related to a variety of different defects and/or charge states. The emission of the 552.1 and 556.8 nm lines is reported at the single-photon emitter level, demonstrating that they originate from the same individual defect. This work follows from previous reports on optically active centers in diamond based on group-IV impurities, such as Si,



Ge, and Sn. In perspective, a comprehensive study of this set of defect complexes could bring significant insight on the common features involved in their formation and opto-physical properties, thus offering a basis for the development of a new generation of quantum-optical devices.

**KEYWORDS:** diamond, lead, color centers, single-photon source, ion implantation, photoluminescence

iamond is a promising platform for the development of solid-state quantum devices with applications in quantum information processing and sensing.<sup>1-5</sup> In recent years, the search for optically active defects with appealing properties has led to the discovery of several classes of color centers<sup>6-11</sup> alternative to the widely investigated negatively charged nitrogen-vacancy complex (NV<sup>-</sup> center).<sup>12</sup> This is motivated by the fact that the NV<sup>-</sup> defect, although extremely promising for its peculiar spin features,<sup>13</sup> is limited in several applications by suboptimal opto-physical properties, such as a spectrally broad emission with intense phonon sidebands, the presence of charge state blinking, and a relatively low emission rate.<sup>14–16</sup> In particular, the silicon-vacancy center (SiV)<sup>17</sup> has attracted significant attention due to a near transform-limited emission,<sup>18,19</sup> good photon indistinguishability,<sup>19,20</sup> the capability of coherently controlling its spin properties,<sup>21–24</sup> and the emergence of reliable techniques for its deterministic fabrication.<sup>25–28</sup>

The recently explored emitters related to group-IV impurities, such as the germanium-related (GeV)<sup>29-31</sup> and tin-related (SnV)<sup>32-34</sup> color centers, are characterized by

similar defect structure and opto-physical properties to those of the SiV center, such as photostability, narrow zero-phonon line (ZPL), relatively small phonon coupling, and high emission rate. This brings further interest in this class of optically active defects. In particular, these recent discoveries open the question of whether the whole set of group-IV-based complexes (SiV, GeV, SnV, and now PbV) result in stable optically active emitters, and second whether the properties of these color centers exhibit any common features.

In this work, we present evidence of photoluminescence (PL) emission from color centers created upon the implantation of Pb ions in diamond followed by thermal annealing. To the best of the authors' knowledge, in a recent work<sup>35</sup> promisingly similar results were obtained from lowfluence Pb implantations in diamond, although with several differences, which could be ascribed to different experimental conditions (excitation wavelengths, spectral filtering, measurement temperature).

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**Figure 1.** (a) PL emission spectra under 532 nm laser excitation from group-IV-related impurities upon ion implantation in the  $(1-10) \times 10^{12}$  cm<sup>-2</sup> fluence range: SiV (ZPL at 738 nm), GeV (602 nm), SnV (620 nm), and the newly reported Pb-related (main emission line at ~552 nm, red curve) centers. (b) Typical PL spectrum under 532 nm laser excitation of a detector-grade diamond substrate (sample #1) implanted with 30 keV PbO<sub>2</sub><sup>-</sup> ions at a 2 × 10<sup>13</sup> cm<sup>-2</sup> fluence.



**Figure 2.** (a) PL emission spectra under 532 nm laser excitation of  $PbO_2^-$ -implanted diamond (sample #3) at increasing ion fluences in the (5–200) × 10<sup>11</sup> cm<sup>-2</sup> range (red, purple, and blue lines). Additional PL spectra acquired from different regions of the same substrate are reported for the sake of comparison: unirradiated diamond (black line) and implanted with 15 keV C<sup>-</sup> (3 × 10<sup>15</sup> cm<sup>-2</sup> fluence, gray line). (b) PL spectra under 532 nm laser excitation of diamond implanted with 30 keV PbO<sub>2</sub><sup>-</sup> (sample #1) and 15 keV Pb<sup>-</sup> ions (sample #3), respectively, at 2 × 10<sup>13</sup> and 3 × 10<sup>12</sup> cm<sup>-2</sup> fluences.

## ENSEMBLE PL EMISSION

**Samples Processing.** The defect fabrication was performed by implanting 35 keV  $PbO_2^-$  (sample #1) and 20 keV  $Pb^-$  (samples #2, #3) ions at different fluences in three CVDgrown single-crystal IIa diamond substrates supplied by ElementSix. The substrates were characterized respectively by "electronic" (substitutional N and B concentration:  $[N_S] < 5$  ppb,  $[B_S] < 5$  ppb, samples #1 and #2 in the following) and "optical" ( $[N_S] < 1$  ppm,  $[B_S] < 0.05$  ppm, sample #3) grades. The utilization of a  $PbO_2^-$  beam was motivated by the low electron affinity of Pb, resulting in relatively small and highly unstable currents achievable for the implantation of elemental ions.<sup>36</sup> The chosen molecular beam thus ensured the achievement of relatively higher implantation fluences for the ensemble characterization of Pb-related defects.

Additional implantations of group-IV-related elements were performed to provide a suitable comparison in the present study: 50 keV Si<sup>-</sup> ( $5 \times 10^{12}$  cm<sup>-2</sup> ion fluence, sample #1), 40 keV Ge<sup>-</sup> ( $1 \times 10^{13}$  cm<sup>-2</sup>, sample #3), and 60 keV Sn<sup>-</sup> ( $1 \times 10^{12}$  cm<sup>-2</sup>, sample #1). The implantation was followed by a thermal annealing at 1200 °C under vacuum (2 h) and by an oxygen plasma treatment, which ensured the removal of

background fluorescence associated with graphitic and organic contaminations of the sample surface.

Room-Temperature PL Emission. A typical roomtemperature PL spectrum acquired by confocal microscopy from an ensemble of centers in sample #1 (2  $\times$  10<sup>13</sup> cm<sup>-</sup> implantation fluence) under 532 nm laser excitation is reported in Figure 1 (red line), together with those of SiV (ZPL at 738 nm), GeV (602 nm), and SnV (620 nm) centers (black lines) for the sake of comparison. The most apparent spectral features associated with Pb implantation (Figure 1b) consist of an intense doublet at 552.1 nm (labeled as  $E_{Pb1}$  in the following) and 556.8 nm  $(E_{Pb2})$  followed by a broader emission band  $(B_{Pb})$  roughly comprised between 565 and 600 nm. These spectral structures show a striking resemblance to that observed for the SiV, GeV, and SnV centers, where the emission is mainly concentrated at the ZPL, with a less pronounced phonon sideband. Indeed, a common trend in the reported spectra is represented by the fact that the intensity of the phonon sidebands increases for heavier impurities (Figure 1a). Furthermore, the heaviest known group-IV-related center reported before the present work, i.e., the SnV defect, also displays a ZPL doublet fine structure at cryogenic temperatures, indicating that the center could have a split ground



**Figure 3.** Temperature-dependent PL spectroscopy under 514 nm laser excitation from  $PbO_2^-$ -implanted diamond: (a) Pb-related emission in the 535–600 nm spectral range at 273, 213, and 143 K; temperature-dependent ZPL position of (b)  $E_{Pb1}$ ,  $E_{Pb2}$ , and first-order Raman emissions; (c)  $E_3$  and  $E_4$  emission, the former displaying a fine structure at T < 200 K; (d)  $E_5$  and  $E_6$  emissions. The dotted lines delimit the fwhm's of the corresponding peaks. The dashed-dotted lines indicate the linear fit of the emission shift.

(and/or excited) state. Apart from this, it is worth remarking that the ZPL wavelength does not follow a systematic spectral shift when considering heavier impurities. This observation is in line with the theoretical calculations reported in ref 37 despite a noticeable mismatch with the experimental value of the ZPL. In addition to the aforementioned spectral features, less intense sharp lines are observed at 539.4 and 574.5 nm ( $E_3$  and  $E_4$  peaks in the following).

A spectral feature similar to the  $E_3$  line has previously been reported in natural diamond upon ion irradiation and hightemperature (>1400 °C) annealing, and tentatively attributed to interstitial-carbon-related defect complexes.<sup>16</sup> However, these previous observations were limited to the cathodoluminescence regime, and the lack of clear evidence of its activity under PL excitation cannot rule out the attribution of the  $E_3$ spectral line to a Pb-related defect.

Conversely, the  $E_4$  emission is tentatively attributed on the basis of temperature-dependent measurements (see below) to the ZPL of the NV<sup>0</sup> center, formed upon the introduction of vacancies in the diamond lattice and the subsequent thermal process. It is also worth mentioning that additional room-temperature spectra acquired in the 700–750 nm range under 532 nm excitation (not shown here) did not reveal any PL

emission around  $\sim$ 715 nm, differently from what was reported in ref 35.

Attribution to Pb-Related Lattice Defects. In order to attribute the spectral features reported in Figure 1 to Pbrelated color centers, in sample #1 the intensity of the PL emission was correlated with the implantation fluence in the  $(5-200) \times 10^{11}$  cm<sup>-2</sup> range. The corresponding PL spectra are shown in Figure 2a. The aforementioned  $E_{Ph1}-E_{Ph2}$  and  $B_{Ph}$ features are absent in the spectrum acquired from a pristine reference region of the substrate, and conversely they exhibit a systematically increasing intensity at increasing implantation fluences. Furthermore, the absence of the  $E_{Ph1}$  and  $E_{Ph2}$  lines is apparent in a control spectrum acquired from a region of the same diamond substrate implanted with 15 keV C<sup>-</sup> ions (3 ×  $10^{15}$  cm<sup>-2</sup> fluence, Figure 2a). It is also worth remarking that the  $E_{pb1}$  and  $E_{pb2}$  emission lines have never been observed in previous reports on diamond crystals implanted with light (H, He) or carbon ions, as well as with other heavier ion species,<sup>5,6,16,38</sup> thus indicating that these spectral features cannot be attributed to intrinsic radiation-induced defects and that the Pb impurities are directly involved in the formation of stable color centers.

 $Pb^-$  vs  $PbO_2^-$  lon Implantation. The aforementioned data were acquired on a  $PbO_2^-$  -implanted substrate. We show

in Figure 2b that the reported spectral features (E<sub>Pb1</sub>, E<sub>Pb2</sub>, E<sub>3</sub>,  $E_4$ ) are left unchanged for both  $PbO_2^-$  and  $Pb^-$  ion implantations. This represents an additional experimental evidence that confirms their attribution to Pb-related optical centers and that the presence of implanted O ions does not modify the relevant emission features, at least for the adopted thermal processing parameters. This result also has a significant technical relevance since, in the perspective of the systematic employment of ion implantation for the creation of Pb-related defects, the technical challenges in the transport and acceleration of a stable Pb<sup>-</sup> beam could significantly affect the fluence control for the deterministic creation of color centers at low implantation fluences. In this sense, apart from providing a useful contribution to unequivocally attribute the luminescent centers to Pb-based defects, the employment of a PbO<sub>2</sub><sup>-</sup> beam also offers a convenient technological solution for the practical fabrication of these defects with ion implantation by taking advantage of more stable ion beams and higher currents.

Temperature-Dependent PL Emission. In order to better investigate the fine structure of the spectral features observed in Pb-implanted diamond, PL spectra under 514 laser excitation were acquired at temperatures in the range comprised between 143 and 273 K (Figure 3a). As typically observed in low-temperature PL experiments, the E<sub>Pb1</sub>, E<sub>Pb2</sub>, E3, and E4 PL peaks increase in intensity and reduce their spectral width with respect to room temperature. All the relevant Pb-related emission peaks display a blue-shift at decreasing temperature (Figure 3b-d). This observation is in qualitative agreement with the attribution of the PL peaks to stable lattice defects, whose chemical bonds are shortened at decreasing temperature.<sup>39</sup> It is worth noting that at 273 K the main emission peak E<sub>Pb1</sub> overlaps with the first-order Raman line (552.4 nm) under 514 nm excitation, and its spectral position can be accurately determined only at temperatures below 233 K. As the temperature decreases, its position reaches a value of 550.9 nm at 143 K. Similarly, at the same temperature the  $E_{Pb2}$  and the  $E_4$  peak blue-shift to 554.9 and 573.7 nm (Figure 3a,b), respectively. None of these emissions exhibit a fine structure in the probed temperature range. The  $E_{Pb2}$ ,  $E_3$ , and  $E_4$  peaks exhibit a linear temperature-dependent shift in the 250-300 K range. This behavior is in good agreement with the linear dependence observed in the same temperature range in previous reports for the other group-IVrelated color centers in diamond.<sup>40-42</sup> A linear fitting (dashed green lines in Figure 3b-d) was therefore performed in this temperature interval to provide a preliminary assessment and comparison. The  $E_{Pb2}$  and the  $E_3$  peak displayed respective slopes of  $12 \pm 5$  and  $12 \pm 1$  pm K<sup>-1</sup>, corresponding to  $47 \pm 5$ and 46  $\pm$  5  $\mu$ eV K<sup>-1</sup>. These values are in the same range (i.e., 9–14 pm  $K^{-1}$ ) as those reported for the SiV, GeV, and SnV centers.<sup>40–42</sup> Furthermore, the compatible energy shift of the  $E_{Pb2}$  and  $E_3$  lines suggests that the emission might originate from the very same defect complex. Conversely, the E<sub>4</sub> temperature shift of 6  $\pm$  1 pm K<sup>-1</sup> (corresponding to 29.7  $\pm$ 3  $\mu$ eV K<sup>-1</sup>) indicates that the emission might be related to a different lattice defect, as supported by the following investigation at the single-photon emitter level. Moreover, this value is comparable with the value of 6.8  $\pm$  0.1 pm  $K^{-1}$ obtained from a linear fitting of the data reported in ref 43 on the temperature dependence of the NV<sup>0</sup> center. On the basis of this agreement, as well as of the striking similarity in the spectral position at 575 nm, the safest attribution of the E<sub>4</sub>

peak is therefore the ZPL of the NV<sup>0</sup> center, as suggested in ref 35, despite the fact that its peculiar phonon sidebands at higher wavelengths could not be unambiguously observed in our PL spectra. A systematic study of the  $E_{Pb1}$  (partially overlapping with the first-order Raman line) was not possible, as the emission of the latter displayed a low intensity in the 250–300 K range, i.e., where a linear behavior is expected.<sup>42</sup>

Conversely, at 143 K the  $E_3$  peak reveals a splitting into two separate lines (i.e., 537.5 and 538.2 nm, Figure 3c). An additional emission peak located at ~592 nm is superimposed to the second-order Raman features (~590–600 nm) and lies in the same spectral position of radiation-induced defects in diamond based on interstitials.<sup>44</sup> Therefore, an estimation of its intensity trend at decreasing temperatures and its unambiguous interpretation in relation to the  $E_{Pb1}$ – $E_{Pb2}$  lines were not possible.

Finally, it is worth remarking that at 143 K two additional spectral lines (i.e., 640.4 and 649.8 nm, labeled as  $E_5$  and  $E_6$  in the following) become visible. Consistently with the above-reported peaks, these spectral features also exhibit a blue-shift at decreasing temperatures (Figure 3d). Furthermore, they were also detected under 405 nm laser excitation, as will be discussed in the following.

**PL under 405 nm Laser Excitation.** Figure 4 shows a typical room-temperature PL spectrum in the 450–675 nm



Figure 4. Ensemble PL emission from sample #1 ( $PbO_2^-$  implantation fluence: 2 × 10<sup>13</sup> cm<sup>-2</sup>) acquired under 405 nm laser excitation.

range acquired under 405 nm laser excitation with a >450 nm long-pass filter. Most notably, the intense emission doublet at 520 nm reported in ref 35 as the ZPL of the PbV center could not be observed.

The  $E_{Pb1}$ ,  $E_{Pb2}$ , and  $E_3$  peaks are still visible, although with a reduced intensity with respect to the  $E_4$  spectral line. It is worth mentioning that  $E_{Pb1}$  and  $E_{Pb2}$  are convoluted due to the limited spectral resolution of the experimental setup adopted for these measurements (i.e., ~4 nm). While the presence of the relevant Pb-related lines confirms the excitability of the optical centers at >3 eV excitation energy, their decreased intensity is compatible with the predicted ionization energy of ~2.6–2.71 of the negative charge state of the PbV center.<sup>35,37</sup> This interpretation is in agreement with the low PL intensity of the spectral features in the 550–560 nm range observed under 450 nm laser excitation at 4 K.<sup>35</sup> Such features should be identified with the  $E_{Pb1}$  and  $E_{Pb2}$  lines reported here.



**Figure 5.** (a) Background-subtracted confocal PL map acquired under 532 nm laser excitation from a region implanted with  $PbO_2^{-}$  at  $5 \times 10^{10}$  cm<sup>-2</sup> fluence. (b) Background-subtracted PL spectrum acquired from the isolated spot circled in blue in (a). The spectrum acquired from the spot and the background spectrum are displayed in the inset (black and red line, respectively). (c) Background-subtracted measurement of the second-order autocorrelation function acquired from the same spot. The black line indicates the corresponding three-level model fitting function. (d) Emission rate of an individual Pb-related defect as a function of the 532 nm laser excitation power. The red line represents the fitting curve.

Furthermore, the  $E_5$  (641.8 nm at room temperature) and  $E_6$ (647.8 nm) emissions are visible, together with a less intense additional feature at 670.8 nm. These lines, which are also reported from Pb-implanted diamond under 450 nm laser excitation at 4 K,<sup>35</sup> are not observable under 532 and 514 nm excitations at room temperature and barely detectable at 143 K under the same excitation wavelengths, while they instead represent the main spectral components of an articulated series of peaks in the 600-700 nm range under 405 nm excitation. While several radiation-induced defects have been studied in this spectral region,<sup>16</sup> to the best of the authors' knowledge no simultaneous detection of both E5 and E6 has been reported so far. In our view, the tentative attribution of E5 to the negative charge state of the NV center (638 nm) in ref 35 is not sufficiently convincing, since no apparent phonon sidebands could be detected and since the NV<sup>-</sup> center is ionized (and therefore not optically active) under 405 nm excitation.<sup>45</sup> Therefore, their attribution to Pb-related defects cannot be ruled out, although such an attribution is still fairly tentative and undoubtedly requires further verification. The significant increase in the E5 and E6 lines' intensity under higher excitation energy might also suggest their interpretation as a different charge state of the same defect(s) associated with the E<sub>Pb1</sub>-E<sub>Pb2</sub> emission.

## SINGLE-PHOTON PL EMISSION

Spectral Analysis. The photoluminescence of Pb-related defects was characterized at the single-photon emitter level at the outer edge of a region implanted with  $PbO_2^-$  ions at 5 ×  $10^{10}$  cm<sup>-2</sup> fluence (sample #1). PL maps were acquired using a confocal microscope under 532 nm CW laser excitation (0.5 mW power on the sample surface) and a set of optical filters, thus enabling the collection of photons at >550 nm wavelengths. A systematic investigation under 405 nm laser excitation was not possible due to the significantly attenuated PL intensity of the relevant emission lines  $(E_{Pb1}, E_{Pb2}, E_3)$ , possibly due to the ionization of the defect. Figure 5a displays a typical PL map, in which individual emitting spots are distributed with a  $\sim 1 \ \mu m^{-2}$  areal density. Assuming a reduction in the Pb concentration of a factor of ~10 with respect to the region implanted at the nominal fluence value, a preliminary estimation of the Pb-related centers' formation efficiency under the adopted thermal processing parameters results in a  $\sim 2\%$  value, which is approximately in line with previous reports in the scientific literature on group-IV-related impurities.<sup>26,32</sup> A dedicated study relying on a deterministic implantation process would provide a more accurate estimation of the efficiency and thus enable optimizing the thermal annealing process to further enhance this parameter.

Figure 5b shows the room-temperature emission spectrum acquired from the bright spot highlighted by the green circle in

Figure 5a. The background spectrum acquired from an unimplanted region was subtracted from the reported spectrum to suppress the first- (572 nm) and second-order (~610-620 nm) Raman scattering features; the unprocessed spectra are visible in the inset of Figure 5b. The emitter exhibited both the  $E_{Pb1}$  and  $E_{Pb2}$  lines, with a clear spectral separation at room temperature. Conversely, the attribution of the  $E_3$  line could not be further addressed, as its emission was filtered out with the adopted >550 nm spectral filtering. On the other hand, its splitting at low temperatures might also indicate a common origin from the very same Pb defect responsible for the  $E_{Pb1}$  and  $E_{Pb2}$  emissions. The concurrent observation of the  $E_{Pb1}$  and  $E_{Pb2}$  PL peaks at the single-photon emitter level offers further elements for their attribution, although three different interpretations could be justified on the basis of the theoretical models available from the literature.<sup>35,</sup>

The spectral position of the PbV ZPL at ~517 nm predicted in ref 37 is not compatible with the data presented in this work. On the other hand, the model reported in ref 35 indicates an intermediate value (~544 nm) between the experimental lines E<sub>Pb1</sub> and E<sub>3</sub>, so that it cannot be regarded as a useful disambiguation. As a first hypothesis, the  $E_{Pb1}$  and  $E_{Pb2}$  lines (spectral separation: ~17.5 meV) could be interpreted as a ZPL doublet, based on the prominence of their stronger intensity with respect to the other spectral features at room temperature. This attribution would be consistent with the theoretical prediction of a 4.4 THz (~18.7 meV) ground state splitting reported in ref 37. According to this interpretation, the E<sub>3</sub> doublet line might correspond to a different Pb-related complex which is dissociated at higher annealing temperatures, similarly to the 593.5 nm emission in Sn-implanted diamond.<sup>32,33</sup> Alternatively, the sole  $E_{Pb1}$  line might be regarded as the ZPL, while the  $E_{Pb2}$  would be its phonon replica associated with quasi-local vibrations. This hypothesis is compatible with the expression of the energy shift associated with the interaction with quasi-local vibrations:<sup>16,32,46</sup>

$$\Delta E = [m/3/(M-m)]^{1/2} \omega_{\rm D}$$
(1)

where  $\omega_{\rm D} = 150$  meV is the Debye frequency of diamond and m = 12 and M = 207.2 are the atomic weights of C and Pb, respectively. In this case the energy for the quasi-local vibration is predicted to be ~21.5 meV, in satisfactory agreement with the aforementioned energy separation of ~17.5 meV observed between  $E_{\rm Pb1}$  and  $E_{\rm Pb2}$ . On the other hand, this attribution does not support the prediction of a significant ground state splitting of the center predicted by ref 37. As a third alternative hypothesis, the  $E_3$  line might be interpreted as the ZPL, and the  $E_{\rm Pb1}$  and  $E_{\rm Pb2}$  emissions would correspond to its phonon replicas. This interpretation is consistent with the prediction in ref 37 of strong phonon interaction in the 55–70 meV range. On the other hand, the  $E_3$  splitting (~3 meV) observed at 143 K would be significantly smaller with respect to what is predicted theoretically in ref 37.

Notably, the absence of the  $E_4$  line at the single-photon emitter level reinforces its attribution to the ZPL of the NV<sup>0</sup> center. Interestingly, the PL spectrum at the single-photon emitter level displays a band centered at ~590 nm, also reported in ref 35 under the same excitation wavelength, rather than the whole  $B_{Pb}$  band reported in Figure 1b. This observation suggests that the  $B_{Pb}$  band results from the convolution of the  $E_4$  emission at 575 nm with the aforementioned 590 nm band. Under this hypothesis, the 590 nm band could be interpreted as related to optical phonons with ~145, ~155, or ~200 meV energy upon the attribution of the ZPL to the  $E_{Pb1}$  peak, the  $E_{Pb1}-E_{Pb1}$  doublet, or the  $E_3$  emission, respectively.

Furthermore, no evidence of the  $E_4-E_6$  lines could be observed under the given experimental conditions. This observation reinforces the hypothesis that the latter spectral features might be associated with a different defect type or with a different charge state of the same complex.

**Nonclassical Emission Properties.** The single-photon emission characterization of the probed spot was performed by measuring the second-order autocorrelation function  $g^2(t)^{47}$  under 532 nm excitation at 0.5 mW power. Figure 5c displays the experimental curve obtained upon the subtraction of the above-mentioned background fluorescence associated with the Raman scattering. The optical center displayed a bunching at zero delay time. Having estimated the signal-to-background ratio as  $\rho = S/(S + B) = 0.52$ , the histogram of the measured coincidences C(t) was corrected according to the following expression:<sup>47</sup>

$$g^{(2)}(t) = (C(t) - (1 - \rho^2))/\rho^2$$
(2)

The corrected value  $g^2(t = 0) < 0.5$  indicates evidence of nonclassical emission from the Pb-related center under consideration. The emitter also displayed a significant bunching behavior, which was interpreted in terms of a three-level system according to the fitting function<sup>32</sup>

$$f(t) = 1 - (1 - a_1) \exp(-|t|/\tau_1) + a_2 \exp(-|t|/\tau_2)$$
(3)

The characteristic time associated with the antibunching behavior was estimated as  $\tau_1 = 3.0 \pm 0.6$  ns, in line with the typical emission lifetimes reported for the group-IV-related color centers in diamond.<sup>17,29,32,33</sup> Similarly, Pb-related centers share with the Si-, Ge-, and Sn-related centers a three-level structure.<sup>17,32</sup> We cannot rule out that this observation might originate from an interplay between the  $E_{Pb1}/E_{Pb2}$  doublet with the  $E_3$  emission line, e.g., resulting from an incomplete annealing of the defect under the adopted thermal processing of the substrate.

Figure 5d shows the typical trend of the backgroundsubtracted PL emission intensity I as a function of the laser excitation power P, as acquired from an individual Pb-related center exhibiting a photostable emission. The background was determined by measuring the PL count rate from an unimplanted region under the same experimental conditions. The trend was fitted with the expression<sup>32</sup>

$$I(P) = I_{\text{sat}} P(P + P_{\text{sat}})^{-1}$$
(4)

where the saturation PL intensity and excitation power  $P_{\text{sat}}$ were determined as  $I_{\text{sat}} = (1.04 \pm 0.07) \times 10^6$  photons s<sup>-1</sup> and  $P_{\text{sat}} = 4.0 \pm 0.5$  mW, respectively.

## CONCLUSIONS

We reported on the formation of optically active centers upon the introduction of Pb impurities by  $Pb^-$  and  $PbO_2^-$  ion implantation into both optical- and electronic-grade CVD diamond samples. The emission intensity of the observed PL lines in the 535–675 nm spectral range strongly correlates with the implantation fluence, thus providing a solid indication that such emission originates from stable Pb-containing lattice defects.

From a spectral analysis carried out at the ensemble level, several emission features were identified, i.e., an intense doublet at 552.1 nm (labeled as  $E_{Pb1}$ ) and 556.8 nm ( $E_{Pb2}$ ), less intense lines at 539.4 nm ( $E_3$ ) and 574.5 nm ( $E_4$ ), and a band comprised between 565 and 600 nm ( $B_{Pb}$ ). While the  $E_4$ emission was attributed to the NV<sup>0</sup> ZPL emission on the basis of temperature-dependent measurements, three alternative attributions of the other above-mentioned features were extensively discussed on the basis of theoretical models and preliminary results available from the literature.<sup>35,37</sup> Furthermore, two intense emission peaks at 641.8 and 647.8 nm ( $E_5$ ,  $E_6$ ), barely excitable under 514 nm excitation, were observed under 405 nm excitation and were tentatively attributed to alternative charge state(s) of the same defect complex that is responsible for the  $E_{Pb1}$ – $E_{Pb2}$  emission lines.

The Pb-related luminescence was also measured from individual lattice defects, through the identification of nonclassical emission in second-order autocorrelation measurements in confocal microscopy.

Temperature-dependent spectral measurements indicated a thermal shift of the order of  $\sim 10 \text{ pm K}^{-1}$  for the main emission lines, which is in line with the other demonstrated nanoscale sensors related with group-IV impurities in diamond.<sup>40-42</sup>

These results represent a significant step toward completing the interpretational framework on the optical activity of diamond defects related to group IV impurities. Future studies on the defects' properties at the single-photon emitter level could lead to appealing perspectives in the fields of quantum information processing and quantum sensing. Furthermore, from a fundamental point of view, the mapping and thorough understanding of a general pattern in the opto-physical properties of color centers associated with impurities of the whole group IV could provide an important reference for the study of defects related to other chemical species.

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#### **Author Contributions**

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## Notes

The authors declare no competing financial interest.

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